

# INC6008AC1-T150

FOR HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

AEC-Q101 Compliance

## DESCRIPTION

INC6008AC1 is a silicon NPN epitaxial type transistor.  
It is designed with high collector current and small  $V_{CE(sat)}$ .

## FEATURE

- Super mini package for easy mounting
- High collector current( $I_C=1A$ )
- Low collector saturation voltage

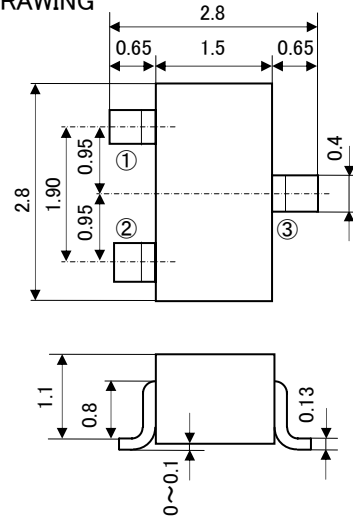
$$(V_{CE(sat)} < 0.7V_{max}, I_C=150mA, I_B=15mA)$$

## APPLICATION

Switching, Small type motor drive

## OUTLINE DRAWING

UNIT : mm



Terminal Connector

- ①: Base  
②: Emitter  
③: Collector

JEITA: SC-59

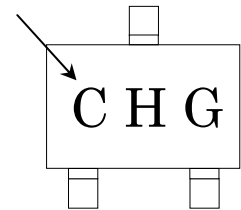
JEDEC: Similar to TO-236

## MAXIMUM RATING ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	RATING	UNIT
$V_{CBO}$	Collector to Base voltage	160	V
$V_{EBO}$	Emitter to Base voltage	5	V
$V_{CEO}$	Collector to Emitter voltage	140	V
$I_C$	Collector current	1	A
$P_C$	Collector dissipation( $T_a=25^\circ\text{C}$ )	200	mW
$T_j$	Junction temperature	+150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-55 ~ +150	$^\circ\text{C}$

## MARKING

Type Name



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

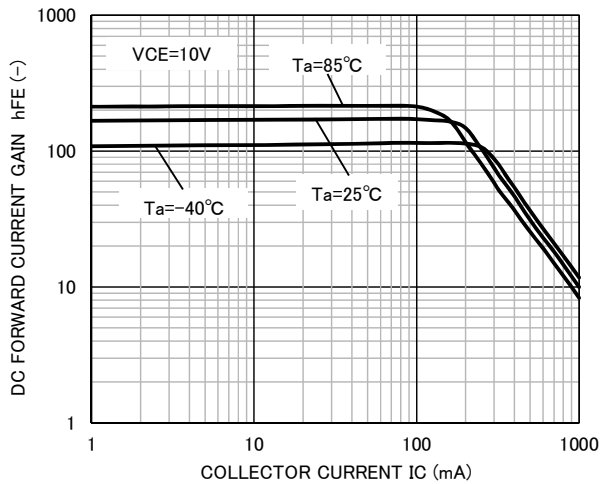
SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
$V_{(BR)CBO}$	C to B breakdown voltage	$I_C=100\mu A, I_E=0mA$	160	-	-	V
$V_{(BR)EBO}$	E to B breakdown voltage	$I_E=100\mu A, I_C=0mA$	5	-	-	V
$V_{(BR)CEO}$	C to E breakdown voltage	$I_C=10mA, R_{BE}=\infty$	140	-	-	V
$I_{CBO}$	Collector cut off current	$V_{CB}=140V, I_E=0mA$	-	-	100	nA
$I_{EBO}$	Emitter cut off current	$V_{EB}=4V, I_C=0mA$	-	-	100	nA
$h_{FE}$	DC forward current gain	$V_{CE}=10V, I_C=150mA$	100	-	300	-
$V_{CE(sat)}$	C to E saturation voltage	$I_C=150mA, I_B=15mA$	-	-	0.7	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C=150mA, I_B=15mA$	-	-	1.1	V
$f_T$	Gain bandwidth product	$V_{CE}=10V, I_E=-50mA, f=100MHz$	100	-	-	MHz
Cob	Collector output capacitance	$V_{CB}=10V, f=1MHz$	-	-	15	pF

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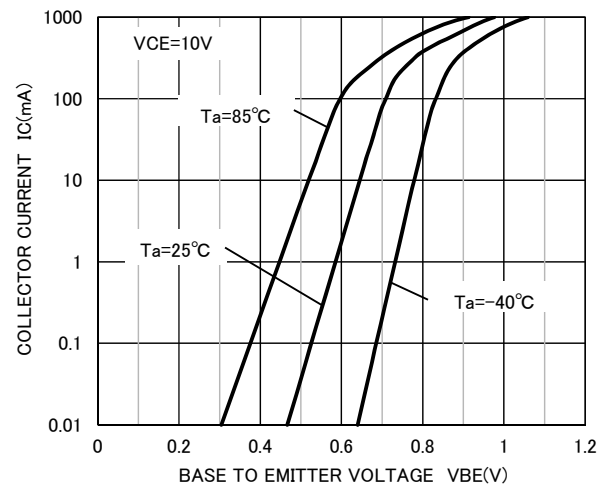
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## TYPICAL CHARACTERISTICS

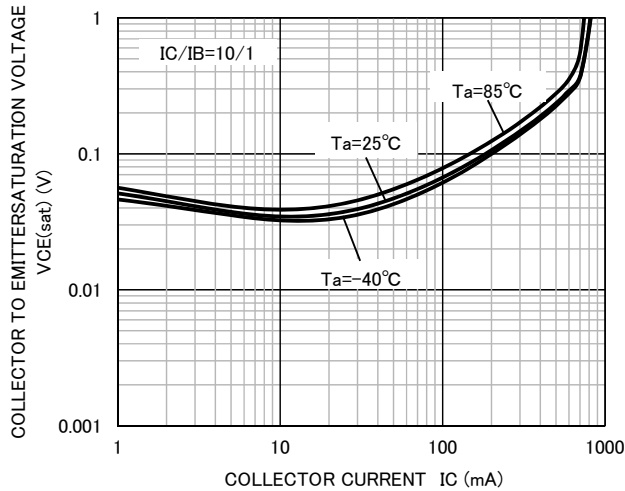
DC FORWARD CURRENT GAIN  
VS. COLLECTOR CURRENT



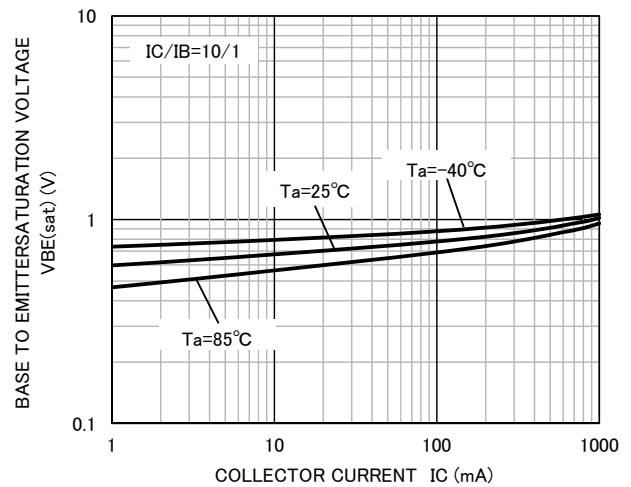
COMMON EMITTER TRANSFER



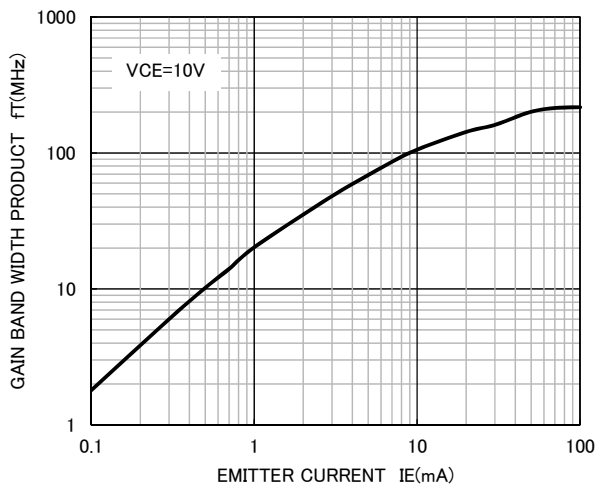
COLLECTOR TO EMITTERSATURATION  
VOLTAGE VS. COLLECTOR CURRENT



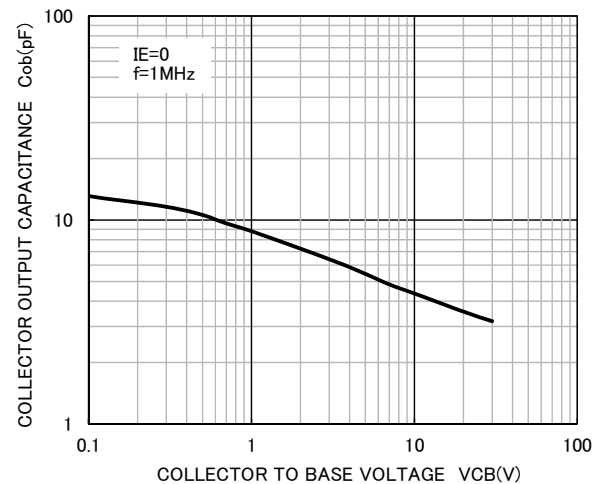
BASE TO EMITTERSATURATION VOLTAGE  
VS. COLLECTOR



GAIN BAND WIDTH PRODUCT  
VS. EMITTER CURRENT

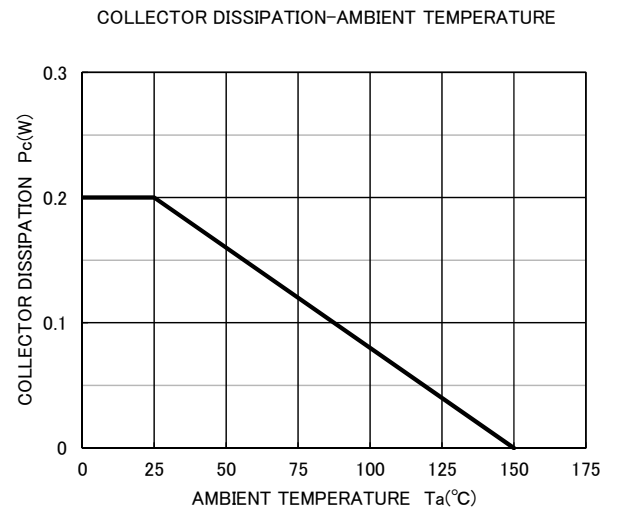
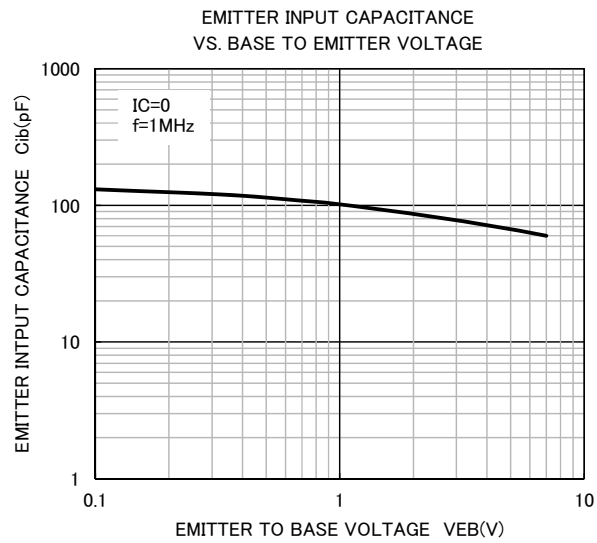


COLLECTOR OUTPUT CAPACITANCE  
VS. COLLECTOR TO BAS



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